Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C. This journal is © The Royal Society of Chemistry 2020





Fig. S1. Schematic diagram of Side view of APON-ST.



Fig. S2. (a)The OM of regularly arranged nanowires, (b) High-resolution O 1S XPS spectra for Ag₂O electrode.



Fig. S3. EPSC triggered by a presynaptic spike (-0.001 V, 50 ms) under the drain voltage of -0.001 V.



Fig. S4. Part of PPF of APON-ST with different interval ($\Delta t = 50 \sim 600 \text{ ms}$).



Fig. S5. Presynaptic spike rate-dependent (SRDP) behavior of APON-ST with different pulses voltage.



Fig. S6. Presynaptic spike duration-dependent (SDDP) behavior of APON-ST



Fig. S7. Presynaptic spike voltage-dependent (SVDP) behavior of APON-ST.



Fig. S8. A transfer curve of APON-ST measured by voltage sweep on the gate (V_G) at a bias voltage of $V_{DS} = -1$ V.



Fig. S9. Bending process diagram of APON-ST.



Fig. S10. Bending process diagram of APON-ST.



Fig. S11. The capacitance as a function of frequency of ion gels.